

Silicon NPN Power Transistors

2SC1140

DESCRIPTION

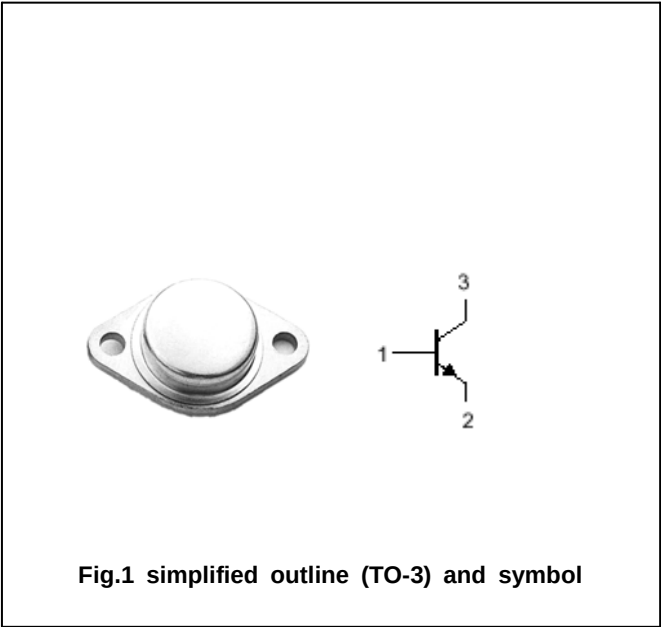
- With TO-3 package
- High voltage ,high speed

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor controls

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V _{CBO}	Collector-base voltage	Open emitter	800	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		15	A
P _T	Total power dissipation	T _{mb} =25℃	150	W
T _j	Junction temperature		200	℃
T _{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-mb}	Thermal resistance from junction to mounting base	1.0	℃/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	400			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =8A ; I _B =1.6A			1.5	V
V _{BESat}	Base-emitter saturation voltage	I _C =8A ; I _B =1.6A			1.6	V
I _{CBO}	Collector cut-off current	V _{CB} =800V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V ; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	15		50	
h _{FE-2}	DC current gain	I _C =7.5A ; V _{CE} =5V	10		25	
f _T	Transition frequency	I _C =1A ; V _{CE} =5V		10		MHz

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PACKAGE OUTLINE

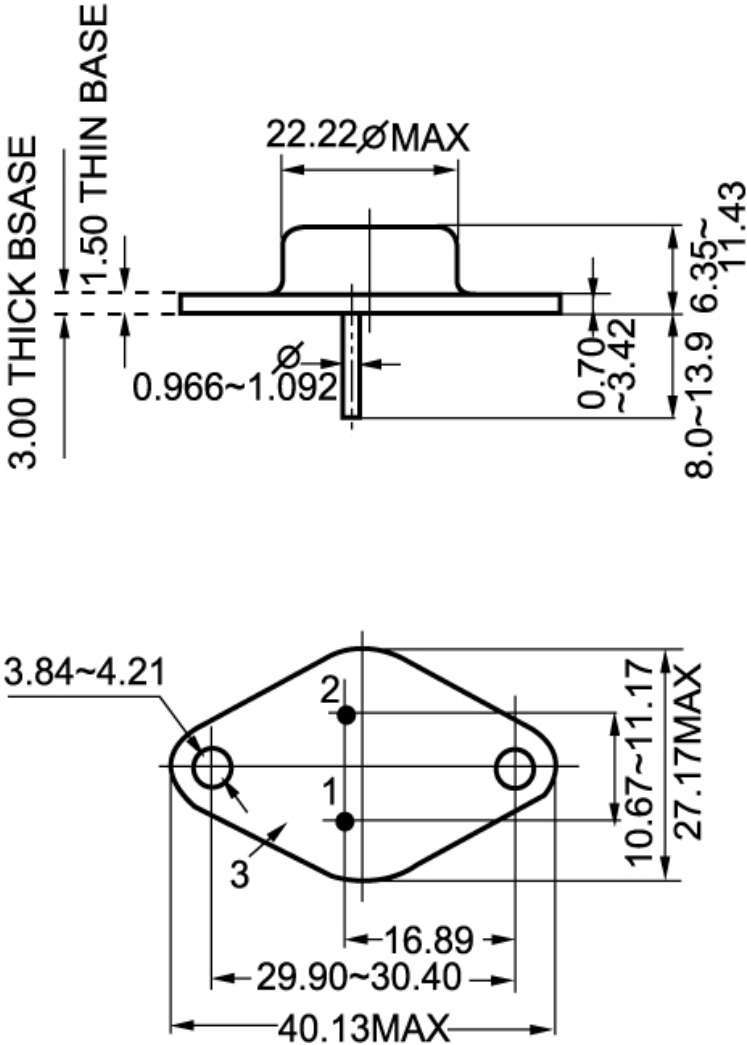


Fig.2 Outline dimensions